## **Electronic Supplementary Information**

## High thermoelectric performance of Ag doped SnTe polycrystalline bulks via the synergistic manipulation of electrical and thermal transport

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Fig. S1 Sn<sub>27</sub>Te<sub>27</sub> (a), Sn<sub>26</sub>Te<sub>27</sub> (b), and Sn<sub>26</sub>AgTe<sub>27</sub> (c) primitive cells used for the DFT calculations, and the 2-dimensional charge density difference for the (001) planes of Sn<sub>27</sub>Te<sub>27</sub> (d), Sn<sub>26</sub>Te<sub>27</sub> (e), and Sn<sub>26</sub>AgTe<sub>27</sub>(f). Blue and yellow colours represent loss and gain of electrons, respectively.



Fig. S2 Calculated electronic band structures for the Sn-deficient  $Sn_{26}Te_{27}$  (a) and silver-doped  $Sn_{26}AgTe_{27}$  (b) using Perdue Burke Ernzerhof generalized gradient approximations (PBE-GGA) based on density functional theory (DFT).



Fig. S3 Calculated partial electronic density-of-states (DOS) for SnTe (a, b) and  $Sn_{26}Te_{27}$  (c, d) based on the DFT method.



Fig. S4 Calculated partial electronic density-of-states (DOS) for the silver doped  $Sn_{26}AgTe_{27}$  based on the DFT method.



Fig. S5 Temperature dependence of the specific heat for the excess-silver-doped  $SnAg_xTe$  (x = 0, 0.01, 0.03, 0.04, 0.10) samples.



Fig. S6 Temperature dependence of the lattice thermal conductivity ( $\kappa_L$ ) for the synthesized SnAg<sub>x</sub>Te (x = 0, 0.01, 0.03, 0.04, 0.10) samples.